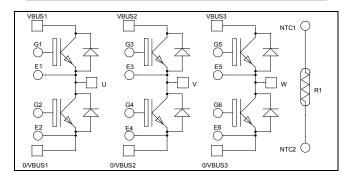
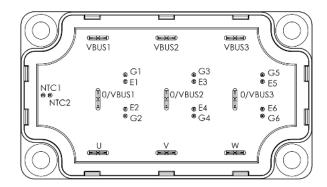


Triple phase leg Trench + Field Stop IGBT4 Power module





Absolute maximum ratings

$V_{CES} = 1200V$ $I_C = 120A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching lossesSoft recovery parallel diodes
 - Soft recovery para
 Low diode VF
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
 - Very low stray inductance - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	140	
I _C	Continuous Collector Current	$T_c = 80^{\circ}C$	120	Α
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	200	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	517	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	200A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electri	cal Characteristics						
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.15	V
V _{CE(sat)}	Conector Emitter saturation voltage	$I_{\rm C} = 100 {\rm A}$	$T_{j} = 150^{\circ}C$		2.15		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3.4 \text{mA}$		5.2	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

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Symbol	Characteristic	Test Conditions	Test Conditions		Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			6.2		
Coes	Output Capacitance				0.4		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz	f=1MHz		0.35		
Q _G	Gate charge	$V_{GE} = \pm 15V$; $V_{GE} = 100A$	$V_{GE} = \pm 15V$; $V_{CE} = 600V$ $I_{C} = 100A$		0.85		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switc	hing (25°C)		130		ns
T _r	Rise Time	$V_{GE} = \pm 15V$			20		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$			300		
T _f	Fall Time	$R_G = 7.5\Omega$			45		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)			150		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$			35		ns
T _{d(off)}	Turn-off Delay Time	$I_C = 100A$			350		115
T _f	Fall Time	$R_G = 7.5\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		5		mJ
Lon	Tuni-on Switching Energy	$V_{Bus} = 600V$	$T_{\rm J} = 150^{\circ}{\rm C}$		10.5		1115
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 100 {\rm A}$	$T_J = 25^{\circ}C$		5.5		mJ
Loff	run-on Switching Energy	$R_G = 7.5\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		9.5		1115
I _{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 10\mu s ; T_j = 1$			400		А

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		-	1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μA
I _F	DC Forward Current		$Tc = 80^{\circ}C$		120		Α
V	Diada Forward Valtaga	$I_{\rm F} = 100 {\rm A}$	$T_i = 25^{\circ}C$		1.9	2.4	V
$V_{\rm F}$	Diode Forward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.85		v
t	Reverse Recovery Time		$T_j = 25^{\circ}C$		155		ns
t _{rr}	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		300		115
0	Q_{rr} Reverse Recovery Charge $V_R = 600V$	$I_{\rm F} = 100 {\rm A}$	$T_j = 25^{\circ}C$		9.3		uС
Qrr		$di/dt = 2400 \text{ A/}\mu\text{s}$	$T_{i} = 150^{\circ}C$		20		μC
Err	Reverse Recovery Energy]	$T_j = 25^{\circ}C$		3.4		mJ
	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		8		1113



Thermal and package characteristics

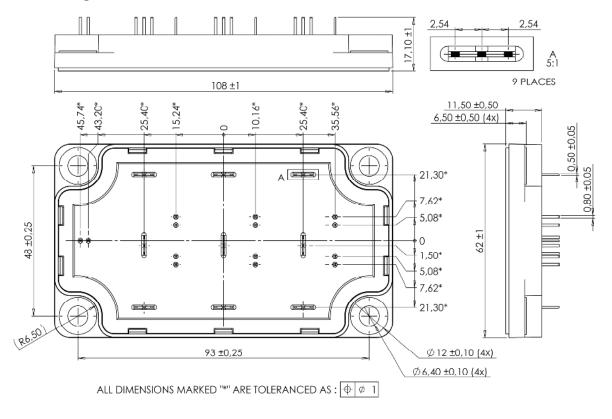
Symbol	Characteristic			Min	Тур	Max	Unit
D	Innetion to Case Thermal Resistance		IGBT			0.29	°C/W
R _{thJC}			Diode			0.5	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range		-40		175		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature		-40		100		
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight				250	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic			Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C				50		kΩ
$\Delta R_{25}/R_{25}$					5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$				3952		Κ
$\Delta B/B$			T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

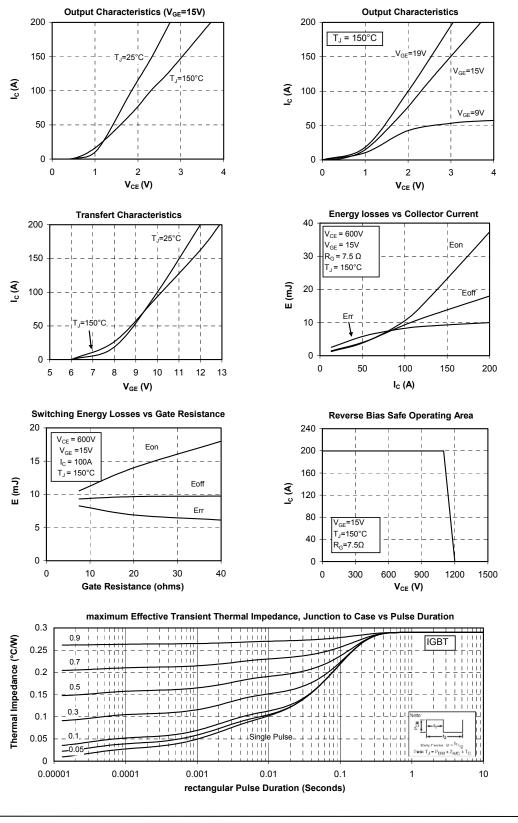
SP6-P Package outline (dimensions in mm)



See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

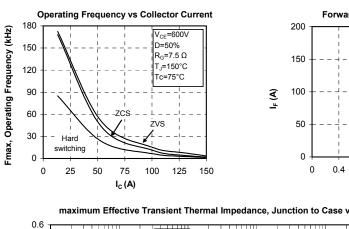


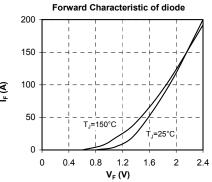
Typical Performance Curve



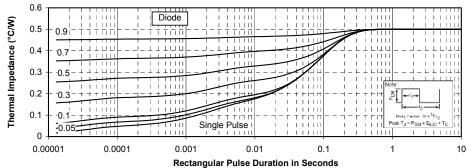
APTGL120TA120TPG-Rev 1 October, 2012







maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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